

1. General description

Planar passivated Silicon Controlled Rectifier in a SOT429N (TO247) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

2. Features and benefits

- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High voltage capacity
- Very high current surge capability

3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging

4. Quick reference data

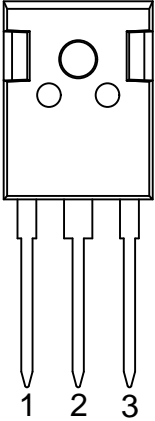

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------|--------------------------------------|--|-----|-----|------|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 1200 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | - | 1200 | V |
| I_{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 1100 | A |
| | | half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$ | - | - | 1210 | A |
| T_j | junction temperature | | - | - | 150 | °C |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{mb} \leq 117\text{ °C}$ | - | - | 80 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_{mb} \leq 117\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 126 | A |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|---|------|-----|-----|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7 ; Fig. 8 | - | - | 70 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 800\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform | 1500 | - | - | V/ μ s |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | K | cathode |  <p style="text-align: center;">TO-247 (SOT429N)</p> |  <p style="text-align: center;">sym037</p> |
| 2 | A | anode | | |
| 3 | G | gate | | |
| mb | A | mounting base; connected to anode | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | Version |
|--------------|---------|---|---------|
| | Name | Description | |
| BT158W-1200T | TO-247 | Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 | SOT429N |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|--|-----|------|--------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 1200 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | 1200 | V |
| $I_{T(AV)}$ | average on-state current | half sine wave; $T_{mb} \leq 117\text{ }^{\circ}\text{C}$ | - | 80 | A |
| $I_{T(RMS)}$ | RMS on-state current | half sine wave; $T_{mb} \leq 117\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 126 | A |
| I_{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5 | - | 1100 | A |
| | | half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$ | - | 1210 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; no voltage reapplied | - | 6115 | A ² s |
| di_T/dt | rate of rise of on-state current | $I_G = 200\text{ mA}$ | - | 150 | A/ μs |
| I_{GM} | peak gate current | | - | 8 | A |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_{GM} | peak gate power | | - | 20 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 1 | W |
| T_{stg} | storage temperature | | -40 | 150 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | - | 150 | $^{\circ}\text{C}$ |

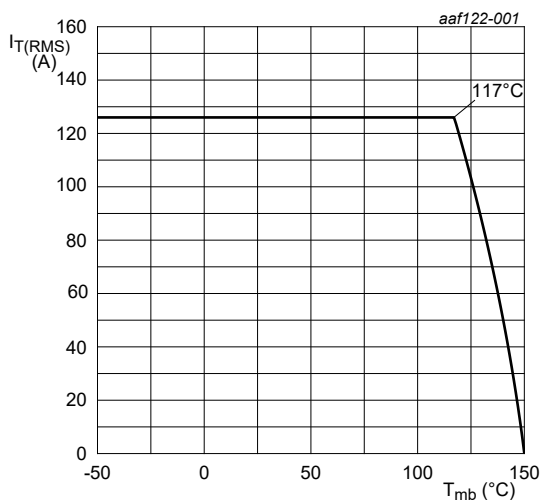
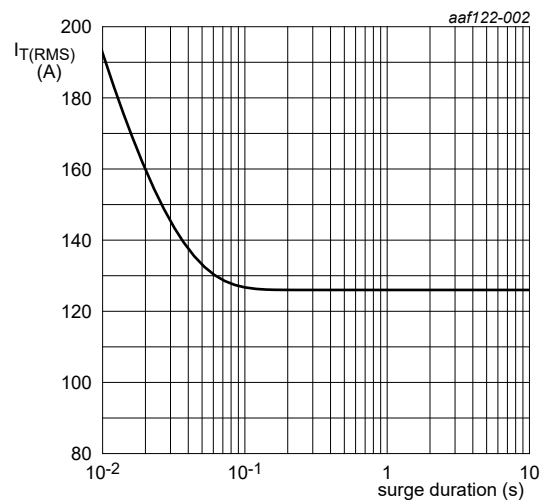
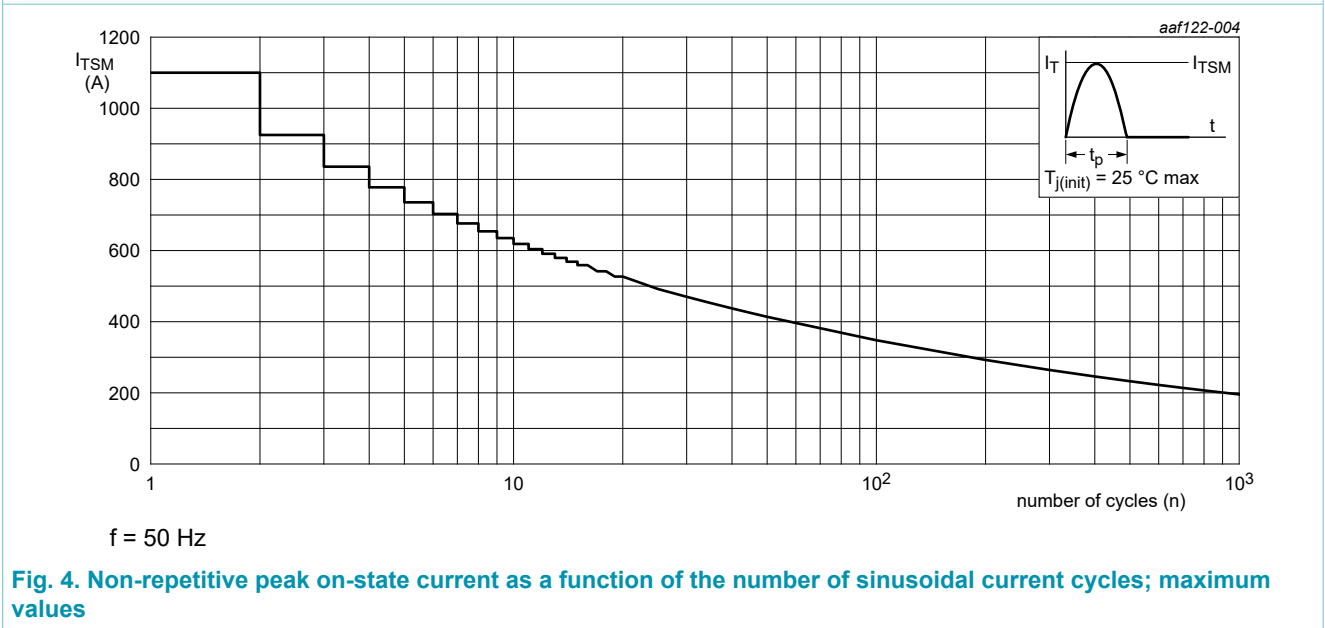
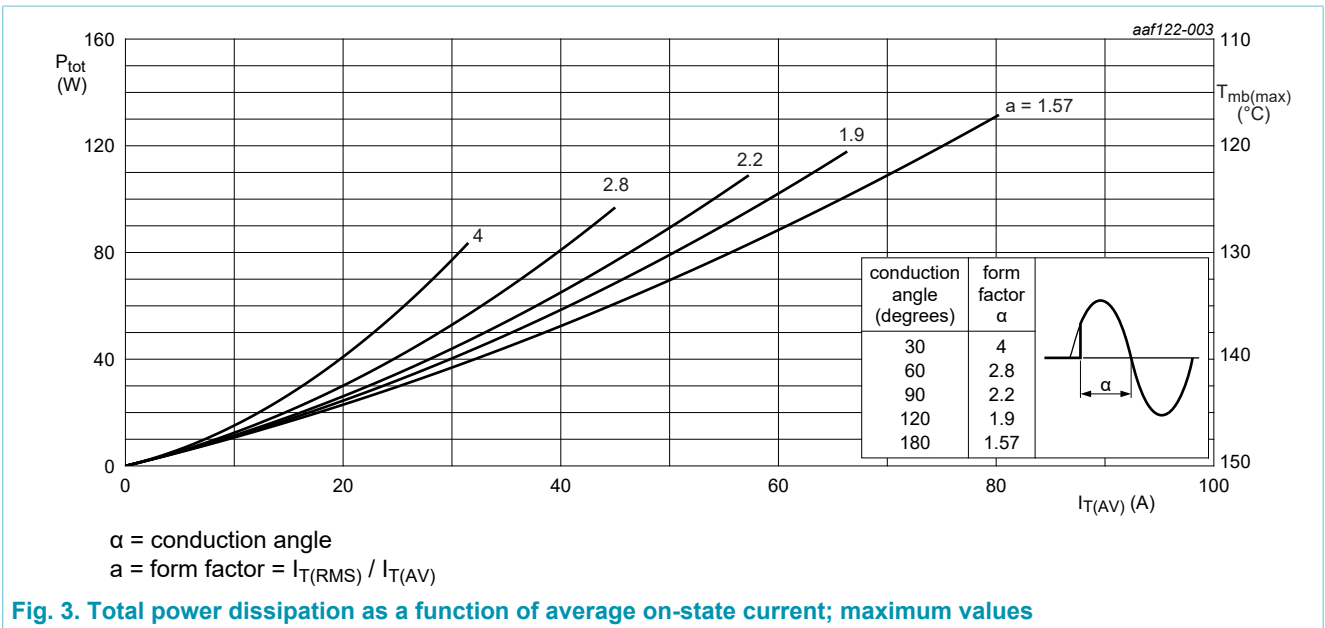


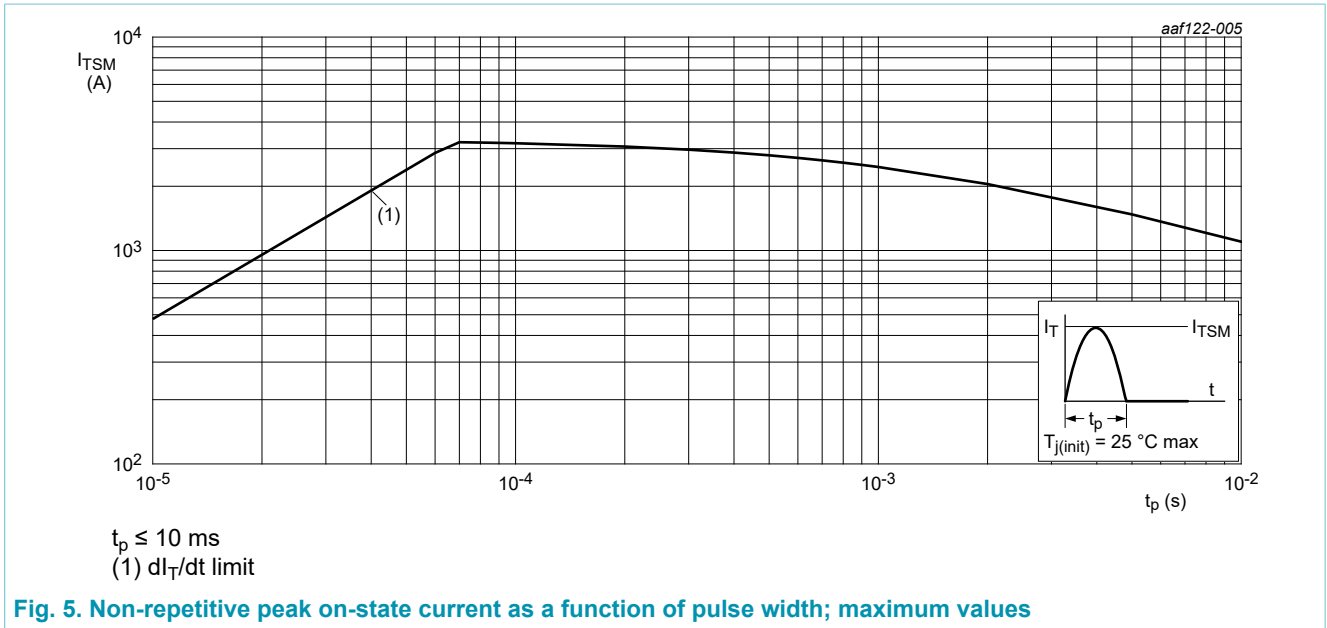
Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} = 117\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values





8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | - | - | 0.25 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 50 | - | K/W |

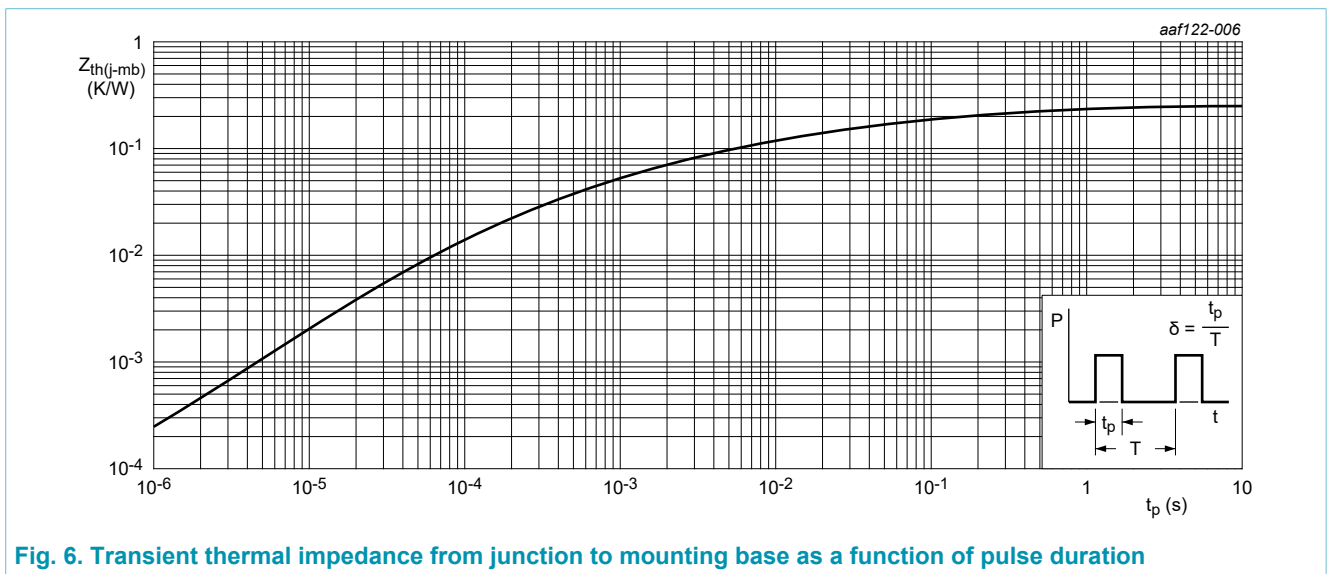


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|--|------|-----|------|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 7 ; Fig. 8 | - | - | 70 | mA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 9 | - | - | 300 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 10 | - | - | 200 | mA |
| V_T | on-state voltage | $I_T = 80\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11 | - | - | 1.35 | V |
| | | $I_T = 160\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11 | - | - | 1.65 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12 | - | 0.7 | 1 | V |
| | | $V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 12 | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = 1200\text{ V}$; $T_j = 125\text{ °C}$ | - | - | 3 | mA |
| I_R | reverse current | $V_R = 1200\text{ V}$; $T_j = 125\text{ °C}$ | - | - | 3 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 800\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform | 1500 | - | - | V/ μ s |
| | | $V_{DM} = 800\text{ V}$; $T_j = 150\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform | 1000 | - | - | V/ μ s |
| t_{gt} | gate-controlled turn-on time | $I_{TM} = 40\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$ | - | 2 | - | μ s |
| t_q | commutated turn-off time | $V_{DM} = 804\text{ V}$; $T_j = 125\text{ °C}$; $I_{TM} = 20\text{ A}$; $V_R = 25\text{ V}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $R_{GK(ext)} = 100\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}) | - | 150 | - | μ s |

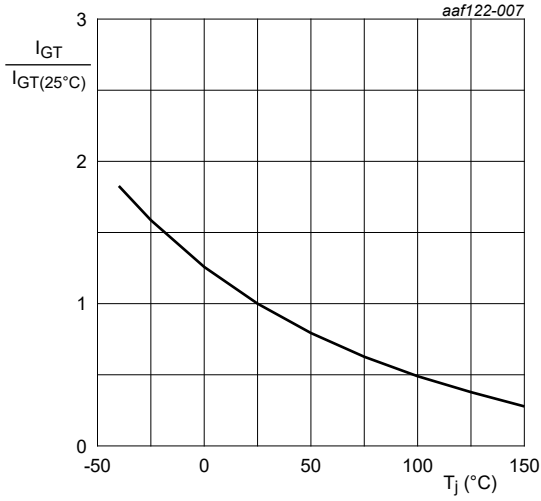


Fig. 7. Normalized gate trigger current as a function of junction temperature

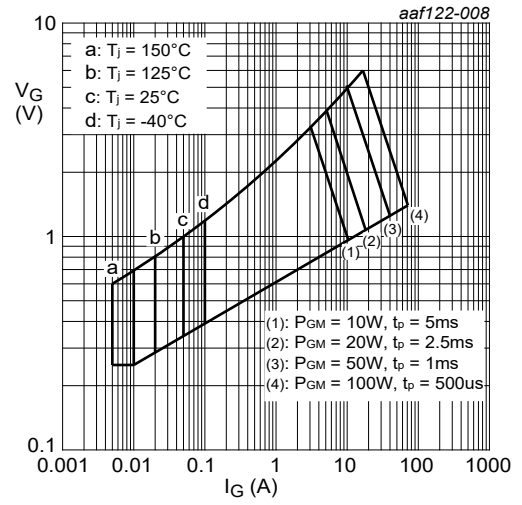


Fig. 8. Gate voltage as a function of gate current

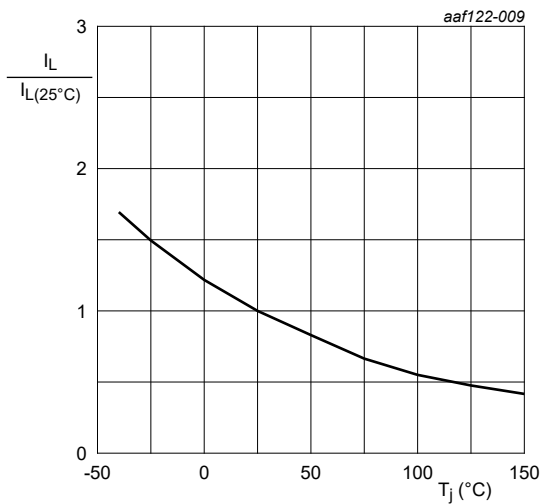


Fig. 9. Normalized latching current as a function of junction temperature

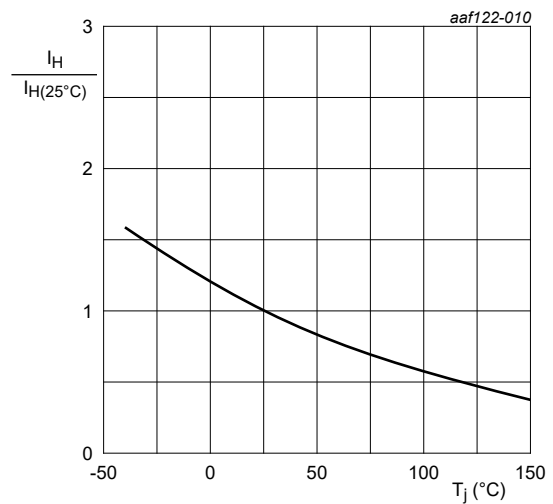
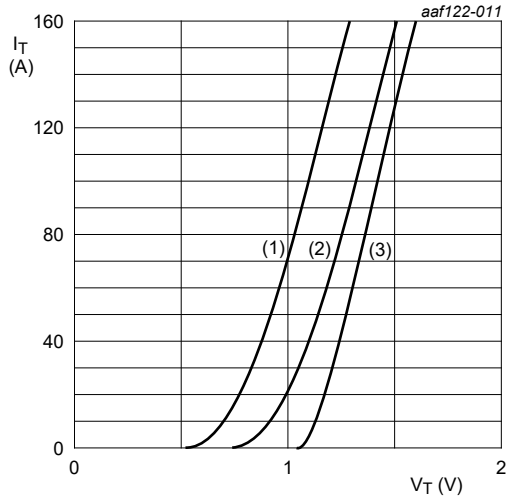


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 0.984 \text{ V}; R_s = 0.0033 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

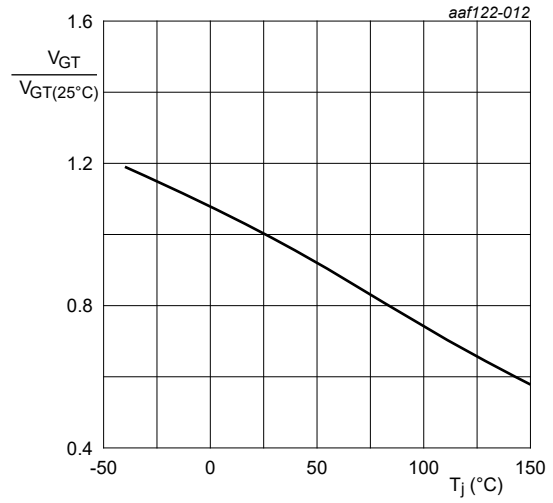


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247

SOT429N

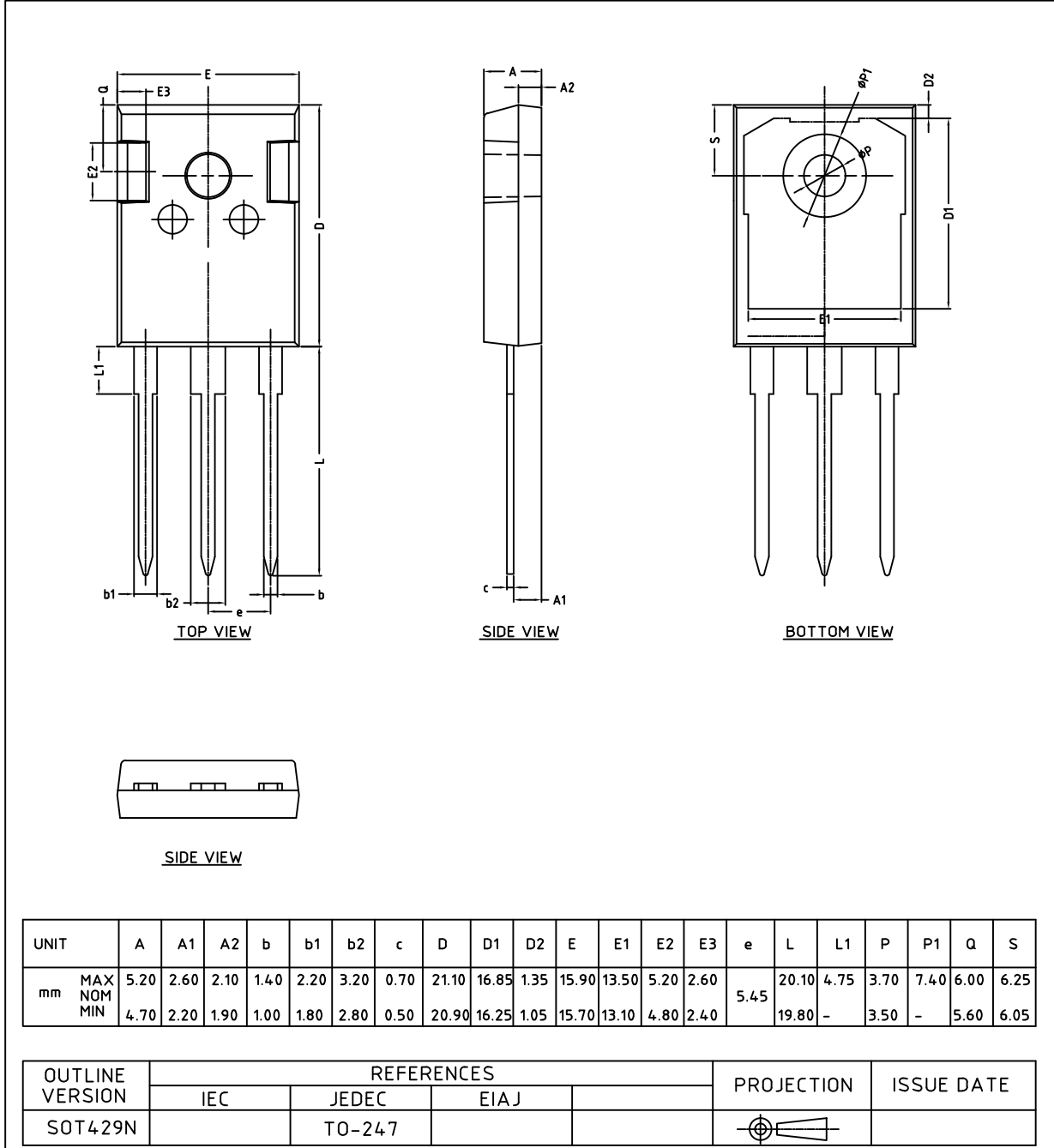


Fig. 13. Package outline TO-247 (SOT429N)

11. Legal information

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|--------------------------------|--------------------|---|
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12. Contents

| | |
|---------------------------------|----|
| 1. General description..... | 1 |
| 2. Features and benefits..... | 1 |
| 3. Applications..... | 1 |
| 4. Quick reference data..... | 1 |
| 5. Pinning information..... | 2 |
| 6. Ordering information..... | 2 |
| 7. Limiting values..... | 3 |
| 8. Thermal characteristics..... | 6 |
| 9. Characteristics..... | 7 |
| 10. Package outline..... | 10 |
| 11. Legal information..... | 11 |

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